

ABSTRACT

WAFER THINNING METHOD

Disclosed herein is a wafer thinning method for thinning a wafer formed from an SiC substrate having a first surface and a second surface opposite to the first surface. The wafer thinning method includes a separation start point forming step of applying the laser beam to the second surface as relatively moving the focal point and the SiC substrate to thereby form a modified layer parallel to the first surface and cracks inside the SiC substrate at the predetermined depth, thus forming a separation start point, and a wafer thinning step of applying an external force to the wafer, thereby separating the wafer into a first wafer having the first surface of the SiC substrate and a second wafer having the second surface of the SiC substrate at the separation start point.

(Figure 11)